





TLV9051, TLV9052, TLV9054 SBOS942J – AUGUST 2018 – REVISED FEBRUARY 2024

TLV9051 / TLV9052 / TLV9054 5MHz, 15V/µs High Slew-Rate, RRIO Op Amp

1 Features

Texas

High slew rate: 15V/µs

INSTRUMENTS

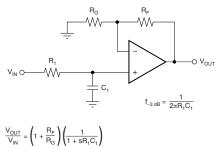
- Low quiescent current: 330µA
- Rail-to-rail input and output
- Low input offset voltage: ±0.33mV
- Unity-gain bandwidth: 5MHz
- Low broadband noise: $15nV/\sqrt{Hz}$
- Low input bias current: 2pA
- Unity-gain stable
- Internal RFI and EMI filter
- Scalable family of CMOS op amps for low-cost applications
- Operational at supply voltages as low as 1.8V
- Extended temperature range: –40°C to 125°C

2 Applications

- HVAC: heating, ventilating, and air conditioning
- Photodiode amplifier
- Current shunt monitoring for DC motor control
- White goods (refrigerators, washing machines, and so forth)
- Sensor signal conditioning
- Active filters
- Low-side current sensing

3 Description

The TLV9051, TLV9052, and TLV9054 devices are single, dual, and quad operational amplifiers, respectively. The devices are designed for low voltage operation from 1.8V to 6.0V. The inputs and outputs can operate from rail to rail at a very high slew rate. These devices are an excellent choice for cost-constrained applications where low-voltage operation, high slew rate, and low quiescent current is needed. The capacitive-load drive of the TLV905x family is 150pF, and the resistive open-loop output impedance makes stabilization easier with much higher capacitive loads.



Single-Pole, Low-Pass Filter

The TLV905xS devices include a shutdown mode that allow the amplifiers to be switched off into a standby mode with typical current consumption less than 1μ A.

The TLV905x family is easy to use due to the devices being unity-gain stable, including a RFI and EMI filter, and being free from phase reversal in an overdrive condition.

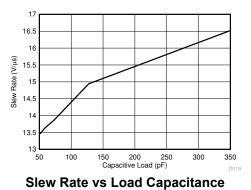
Device Information								
PART NUMBER ⁽¹⁾	CHANNEL COUNT	PACKAGE ⁽²⁾	PACKAGE SIZE ⁽⁴⁾					
		DBV (SOT-23, 5)	2.9mm × 2.8mm					
TLV9051	Single	DCK (SC70, 5)	2mm × 2.1mm					
1209031	Siligie	DRL (SOT553, 5) ⁽³⁾	1.6mm × 1.6mm					
		DPW (X2SON, 5)	0.8mm × 0.8mm					
TLV9051S	Single, Shutdown	DBV (SOT-23, 6)	2.9mm × 2.8mm					
		D (SOIC, 8)	4.9mm × 6mm					
		PW (TSSOP, 8)	3.mm × 6.4mm					
TLV9052	Dual	DGK (VSSOP, 8)	3mm × 4.9mm					
		DDF (SOT-23, 8)	2.9mm × 2.8mm					
		DSG (WSON, 8)	2mm × 2mm					
TLV9052S	Dual. Shutdown	DGS (VSSOP, 10)	3mm × 4.9mm					
11090525	Dual, Shuldown	RUG (X2QFN, 10)	1.5mm × 2mm					
		D (SOIC, 14)	8.65mm × 6mm					
TI 1/0054	Quart	PW (TSSOP, 14)	5mm × 6.4mm					
TLV9054	Quad	RUC (WQFN, 14)	2mm × 2mm					
		RTE (WQFN, 16)	3mm × 3mm					
TLV9054S	Quad, Shutdown	RTE (WQFN, 16)	3mm × 3mm					

(1) See Device Comparison

(2) For more information, see Section 11

(3) Package is for preview only.

(4) The package size (length × width) is a nominal value and includes pins, where applicable.



Device Information



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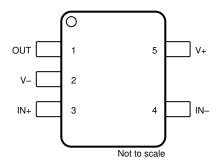
4 Device Comparison Table

		PACKAGE LEADS												
DEVICE	NO. OF CH.	SC70 DCK	SOT-23 DBV	SOT-553 (1) DRL	X2SON DPW	SOIC D	WSON DSG	VSSOP DGK	TSSOP PW	SOT-23 DDF	VSSOP DGS	X2QFN RUG	X2QFN RUC	WQFN RTE
TLV9051	1	5	5	5	5	—	-	—	_	—	_	—	-	_
TLV9051S		—	6	—	_	—	—	—	—	—	—	—	_	_
TLV9052	2	—	—	—	_	8	8	8	8	8	—	—	_	_
TLV9052S	2	—	—	—	—	—	—	—	—	—	10	10	_	_
TLV9054	4	_	_	—	_	14	-	—	14	—	_	_	14	16
TLV9054S	4	—	—	—	_	—	—	—	_	—	_	—	_	16

(1) Package is for preview only.



5 Pin Configuration and Functions



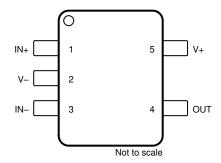




Figure 5-2. TLV9051 DCK Package 5-Pin SC70 Top View

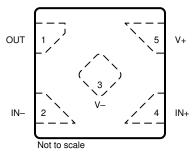


Figure 5-3. TLV9051 DPW Package 5-Pin X2SON Top View

PIN								
NAME	SOT-23, SOT-553	SC-70 X2SON		I/O	DESCRIPTION			
IN–	4	3	2	I	Inverting input			
IN+	3	1	4	1	Noninverting input			
OUT	1	4	1	0	Output			
V–	2	2	3	-	Negative (low) supply or ground (for single-supply operation)			
V+	5	5	5	-	Positive (high) supply			

Table 5-1. Pin Functions: TLV9051



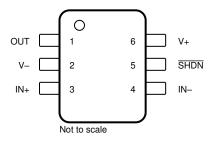




Table 5-2. Pin Functions: TLV9051S

PIN		I/O	DESCRIPTION			
NAME	NO.	1/0	DESCRIPTION			
-IN	4	I	Inverting input			
+IN	3	I	Noninverting input			
OUT	1	0	Output			
SHDN	5	I	Shutdown: low = amp disabled, high = amp enabled. See <i>Section 7.3.9</i> for more information.			
V-	2	—	Negative (lowest) supply or ground (for single-supply operation).			
V+	6	—	Positive (highest) supply			



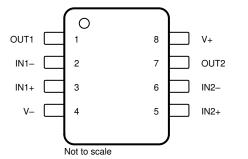
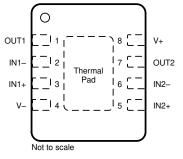


Figure 5-5. TLV9052 D, DGK, PW, DDF Packages 8-Pin SOIC, VSSOP, TSSOP, SOT-23 Top View



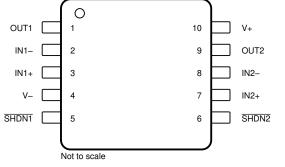


Connect exposed thermal pad to V–. See *Section* 7.3.6 for more information.

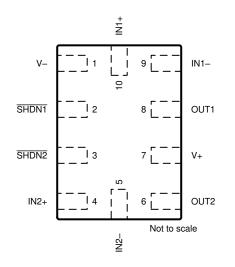
Figure 5-6. TLV9052 DSG Package 8-Pin WSON With Exposed Thermal Pad Top View

	PIN	1/0	DESCRIPTION
NAME	NO.	1.0	DESCRIPTION
IN1–	2	I	Inverting input, channel 1
IN1+	3	I	Noninverting input, channel 1
IN2-	6	I	Inverting input, channel 2
IN2+	5	I	Noninverting input, channel 2
OUT1	1	0	Output, channel 1
OUT2	7	0	Output, channel 2
V–	4	_	Negative (low) supply or ground (for single-supply operation)
V+	8	_	Positive (high) supply

Table 5-3. Pin Functions: TLV9052







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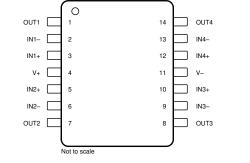
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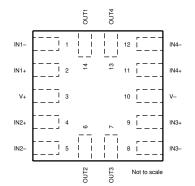
Figure 5-8. TLV9052S RUG Package 10-Pin X2QFN Top View

PIN		I/O	DESCRIPTION	
NAME	VSSOP	X2QFN	1/0	DESCRIPTION
IN1–	2	9	I	Inverting input, channel 1
IN1+	3	10	I	Noninverting input, channel 1
IN2–	8	5	I	Inverting input, channel 2
IN2+	7	4	I	Noninverting input, channel 2
OUT1	1	8	0	Output, channel 1
OUT2	9	6	0	Output, channel 2
SHDN1	5	2	I	Shutdown: low = amp disabled, high = amp enabled, channel 1. See <i>Section</i> 7.3.9 for more information.
SHDN2	6	3	I	Shutdown: low = amp disabled, high = amp enabled, channel 2. See <i>Section</i> 7.3.9 for more information.
V–	4	1		Negative (low) supply or ground (for single-supply operation)
V+	10	7		Positive (high) supply

Table 5-4. Pin Functions: TLV9052S

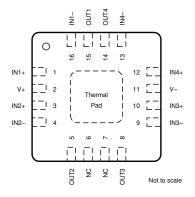












Connect exposed thermal pad to V-. See Section 7.3.6 for more information.

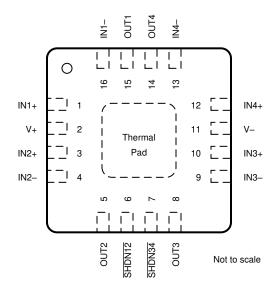
Figure 5-11. TLV9054 RTE Package 16-Pin WQFN With Exposed Thermal Pad Top View

Table 5-5. Pin Functions: TLV9054

PIN					
NAME	SOIC, TSSOP	WQFN	X2QFN	I/O	DESCRIPTION
IN1–	2	16	1	I	Inverting input, channel 1
IN1+	3	1	2	1	Noninverting input, channel 1
IN2-	6	4	5	I	Inverting input, channel 2
IN2+	5	3	4	I	Noninverting input, channel 2
IN3–	9	9	8	I	Inverting input, channel 3
IN3+	10	10	9	I	Noninverting input, channel 3
IN4–	13	13	12	I	Inverting input, channel 4
IN4+	12	12	11	I	Noninverting input, channel 4
NC	_	6, 7	_	_	No internal connection
OUT1	1	15	14	0	Output, channel 1
OUT2	7	5	6	0	Output, channel 2
OUT3	8	8	7	0	Output, channel 3
OUT4	14	14	13	0	Output, channel 4
V–	11	11	10	_	Negative (low) supply or ground (for single-supply operation)
V+	4	2	3	_	Positive (high) supply

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Connect exposed thermal pad to V-. See Section 7.3.6 for more information.

Figure 5-12. TLV9054S RTE Package 16-Pin WQFN With Exposed Thermal Pad Top View

Table 5-6. Pin Functions: TLV9054S

PIN		I/O	DESCRIPTION			
NAME	NO.	- I/O	DESCRIPTION			
IN1+	1	I	Noninverting input, channel 1			
IN1–	16	I	Inverting input, channel 1			
IN2+	3	I	Noninverting input, channel 2			
IN2–	4	I	Inverting input, channel 2			
IN3+	10	I	Noninverting input, channel 3			
IN3–	9	I	Inverting input, channel 3			
IN4+	12	I	Noninverting input, channel 4			
IN4–	13	I	Inverting input, channel 4			
SHDN12	6	I	Shutdown: low = amp disabled, high = amp enabled, channel 1 and 2. See Section 7.3.9 for more information.			
SHDN34	7	I	Shutdown: low = amp disabled, high = amp enabled, channel 3 and 4. See Section 7.3.9 for more information.			
OUT1	15	0	Output, channel 1			
OUT2	5	0	Output, channel 2			
OUT3	8	0	Output, channel 3			
OUT4	14	0	Output, channel 4			
V–	11	_	Negative (low) supply or ground (for single-supply operation)			
V+	2	_	Positive (high) supply			



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature (unless otherwise noted)⁽¹⁾

			MIN	IAX	UNIT
Supply voltage				7	V
	Voltage ⁽²⁾ Current ⁽²⁾ rt-circuit ⁽³⁾ Specified, T _A Junction, T _J	Common-mode	(V–) – 0.5 (V+) +	0.5	V
Signal input pins	Voltage	Differential	(V+) – (V–) +	0.2	v
	Current ⁽²⁾		-10	10	mA
Output short-circuit ⁽³⁾)		Continuous		mA
	Specified, T _A		-40	125	
Temperature	Junction, T _J			150	°C
	Storage, T _{stg}		-65	150	

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Input pins are diode-clamped to the power-supply rails. Current limit input signals that can swing more than 0.5 V beyond the supply rails to 10 mA or less.

(3) Short-circuit to ground, one amplifier per package.

6.2 ESD Ratings

			VALUE	UNIT				
TLV9051 X2SON PACKAGE								
V	Electrostatio discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±3000	V				
V _(ESD) Electrostatic dis	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	v				
ALL OTI	ALL OTHER PACKAGES							
V		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V				
V _(ESD) Electrosta	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	v				

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Vs	Supply voltage, $V_S = (V+) - (V-)$	1.8	6.0	V
V _{IN}	Input pin voltage	(V–) – 0.1	(V+) + 0.1	V
	Specified temperature	-40	125	°C

6.4 Thermal Information for Single Channel

		TLV9051, TLV9051S					
THERMAL METRIC ⁽¹⁾		DPW (X2SON)	DBV (SOT-23)		DCK (SC70)	DRL (SOT553) (2)	UNIT
		5 PINS	5 PINS	6 PINS	5 PINS	5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	470.0	228.1	210.8	231.2	TBD	°C/W
R _{0JC(top)}	Junction-to-case(top) thermal resistance	211.9	152.1	152.1	144.4	TBD	°C/W
R _{θJB}	Junction-to-board thermal resistance	334.8	97.7	92.3	78.6	TBD	°C/W
ΨJT	Junction-to-top characterization parameter	29.8	74.1	76.2	51.3	TBD	°C/W

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6.4 Thermal Information for Single Channel (continued)

		TLV9051, TLV9051S					
	THERMAL METRIC ⁽¹⁾	DPW (X2SON)	DBV (SOT-23)		DBV (SOT-23) DCK (SC70) DRL (S		UNIT
		5 PINS	5 PINS	6 PINS	5 PINS	5 PINS	
Ψ _{JB}	Junction-to-board characterization parameter	333.2	97.3	92.1	78.3	TBD	°C/W
R _{0JC(bot)}	Junction-to-case(bottom) thermal resistance	N/A	N/A	N/A	N/A	TBD	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

(2) This package option is for preview only.

6.5 Thermal Information for Dual Channel

		TLV9052, TLV9052S							
	THERMAL METRIC ⁽¹⁾	D (SOIC)	DGK (VSSOP)	DSG (WSON)	PW (TSSOP)	DDF (SOT-23)	DGS (VSSOP)	RUG (X2QFN)	UNIT
		8 PINS	8 PINS	8 PINS	8 PINS	8 PINS	10 PINS	10 PINS	
R_{\thetaJA}	Junction-to-ambient thermal resistance	155.4	208.8	102.3	205.1	184.4	170.4	197.2	°C/W
R _θ JC(top)	Junction-to-case(top) thermal resistance	95.5	93.3	120.0	93.7	112.8	84.9	93.3	°C/W
$R_{\theta J B}$	Junction-to-board thermal resistance	98.9	130.7	68.2	135.7	99.9	113.5	123.8	°C/W
Ψյτ	Junction-to-top characterization parameter	41.9	26.1	15.1	25.0	18.7	16.4	3.7	°C/W
ΨЈВ	Junction-to-board characterization parameter	98.1	128.9	68.2	134.0	99.3	112.3	120.2	°C/W
R _θ JC(bot)	Junction-to-case(bottom) thermal resistance	N/A	N/A	43.6	N/A	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.6 Thermal Information for Quad Channel

		TLV9054, TLV9054S					
	THERMAL METRIC ⁽¹⁾	D (SOIC)	D (SOIC) PW (TSSOP) RTE (WQFN)		RUC (X2SQFN)	UNIT	
		14 PINS	14 PINS	14 PINS	16 PINS	14 PINS	
$R_{\theta J A}$	Junction-to-ambient thermal resistance	115.0	147.2	65.5	65.6	209.4	°C/W
R _θ JC(top)	Junction-to-case(top) thermal resistance	71.1	67.2	70.6	70.6	68.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	71.0	91.6	40.5	40.5	153.3	°C/W
ΨJT	Junction-to-top characterization parameter	29.7	16.6	5.8	5.8	3.0	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	70.6	90.7	40.5	40.5	152.8	°C/W
R _θ JC(bot)	Junction-to-case(bottom) thermal resistance	N/A	N/A	24.5	24.5	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.



6.7 Electrical Characteristics: V_S (Total Supply Voltage) = (V+) – (V–) = 1.8 V to 5.5 V

at T_A = 25°C, R_L = 10 k Ω connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted);

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET	VOLTAGE	·				
	lument offersteinsteine	V _S = 5 V		±0.33	±1.6	
V _{OS}	Input offset voltage	$V_{\rm S}$ = 5 V, $T_{\rm A}$ = -40°C to +125°C			±2	mV
dV _{OS} /dT	Drift	$V_{\rm S}$ = 5 V, $T_{\rm A}$ = -40°C to +125°C		±0.5		μV/°C
PSRR	Power-supply rejection ratio	V _S = 1.8 V – 5.5 V, V _{CM} = (V–)		±13	±80	μV/V
	Channel separation, dc	At dc		115		dB
	DLTAGE RANGE				I	
V _{CM}	Common-mode voltage	V _S = 1.8 V to 5.5 V	(V–) – 0.1		(V+) + 0.1	V
		$V_S = 5.5 \text{ V}, (V-) - 0.1 \text{ V} < V_{CM} < (V+) - 1.4 \text{ V},$ $T_A = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}$	80	96		
	Common-mode rejection	$V_{S} = 5.5 \text{ V}, V_{CM} = -0.1 \text{ V} \text{ to } 5.6 \text{ V},$ $T_{A} = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}$	62	79		-ID
CMRR	ratio	$V_{S} = 1.8 \text{ V}, (V-) - 0.1 \text{ V} < V_{CM} < (V+) - 1.4 \text{ V},$ $T_{A} = -40^{\circ}\text{C to} +125^{\circ}\text{C}$		88		dB
		$V_{S} = 1.8 \text{ V}, V_{CM} = -0.1 \text{ V} \text{ to } 1.9 \text{ V},$ $T_{A} = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}$		72		
INPUT BI	AS CURRENT					
	Input biog ourset			±2	±18 ⁽²⁾	pA
IB	Input bias current	$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$			±525 ⁽²⁾	pА
				±1	±15 ⁽²⁾	pА
l _{os}	Input offset current	$T_{A} = -40^{\circ}C \text{ to } +125^{\circ}C$			±440 ⁽²⁾	pА
NOISE					I	
En	Input voltage noise (peak- to-peak)	V _S = 5 V, f = 0.1 Hz to 10 Hz		6		μV _{PP}
_		V _S = 5 V, f = 10 kHz		15		nV/√Hz
en	Input voltage noise density	V _S = 5 V, f = 1 kHz		20		nV/√Hz
in	Input current noise density	f = 1 kHz		18		fA/√Hz
INPUT CA	PACITANCE				1	
CID	Differential			2		pF
CIC	Common-mode			4		pF
OPEN-LO	OP GAIN				I	
		$V_{\rm S}$ = 1.8 V, (V–) + 0.04 V < V _O < (V+) – 0.04 V, R _L = 10 kΩ		106		
•	Open-loop voltage gain	$V_{\rm S}$ = 5.5 V, (V–) + 0.05 V < V_{\rm O} < (V+) – 0.05 V, R _L = 10 kΩ	104	128		dB
A _{OL}	Open-loop voltage gain			108		dВ
		V_{S} = 5.5 V, (V–) + 0.15 V < V_{O} < (V+) – 0.15 V, R_{L} = 2 k Ω		130		
FREQUE	NCY RESPONSE					
GBP	Gain bandwidth product	V _S = 5.5 V, G = +1		5		MHz
φ _m	Phase margin	V _S = 5.5 V, G = +1		60		Degrees
SR	Slew rate	V _S = 5.5 V, G = +1, C _L = 130pF		15		V/µs
	Cattling time	To 0.1%, V_S = 5.5 V, 2-V step , G = +1, C_L = 100 pF		0.75		
t _S	Settling time	To 0.01%, V _S = 5.5 V, 2-V step , G = +1, C _L = 100 pF		1		μs
t _{OR}	Overload recovery time	$V_{\rm S}$ = 5.5 V, $V_{\rm IN}$ × gain > $V_{\rm S}$		0.3		μs
THD + N	Total harmonic distortion + noise ⁽¹⁾	V _S = 5.5 V, V _{CM} = 2.5 V, V _O = 1 V _{RMS} , G = +1, f = 1 kHz		0.0006%		
OUTPUT						
.,	Voltage output swing from	V_{S} = 5.5 V, R _L = 10 kΩ,			16	
Vo	supply rails	$V_{\rm S} = 5.5 \text{ V}, \text{ R}_{\rm L} = 2 \text{ k}\Omega,$	1		40	mV

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6.7 Electrical Characteristics: V_S (Total Supply Voltage) = (V+) – (V–) = 1.8 V to 5.5 V (continued)

at $T_A = 25^{\circ}$ C, $R_L = 10 \text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted);

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{SC}	Short-circuit current	V _S = 5 V		±50		mA
Z _O	Open-loop output impedance	V _S = 5 V, f = 5 MHz		250		Ω
POWER	SUPPLY				I	
ı	Quiescent current per	V _S = 5.5 V, I _O = 0 mA,		330	450	
Ι _Q	amplifier	$V_{\rm S}$ = 5.5 V, I _O = 0 mA, T _A = -40°C to +125°C			475	μΑ
SHUTD	OWN					
I _{QSD}	Quiescent current per amplifier	V_{S} = 1.8 to 5.5 V, all amplifiers disabled, SHDN = V-		0.35	1	μΑ
Z _{SHDN}	Output impedance	V _S = 1.8 to 5.5 V, amplifier disabled		10 2		GΩ∥pF
	High-level voltage shutdown threshold (amplifier enabled)	$V_{\rm S}$ = 1.8 to 5.5 V		(V-) + 0.9	(V-) + 1.1	V
	Low-loevel voltage shutdown threshold (amplifeir disabled)	$V_{\rm S}$ = 1.8 to 5.5 V	(V-) + 0.2	(V-) + 0.7		V
t _{ON}	Amplifier enabled time (full shutdown ⁽³⁾ ⁽⁴⁾			35		μS
t _{ON}	Amplifier enabled time (partial shutdown) ^{(3) (4)}			10		μS
t _{OFF}	Amplifier diabled time (3)			6		μS
	SHDN pin input bias current (per pin)	$V_{\rm S}$ = 1.8 V to 5.5 V, V+ \geq (V+) - 0.8 V		6.5		nA
	SHDN pin input bias current (per pin)	$V_{\rm S}$ = 1.8 V to 5.5 V, V+ ≤ (V-) + 0.8 V		155		nA

(1) Third-order filter; bandwidth = 80 kHz at - 3 dB.

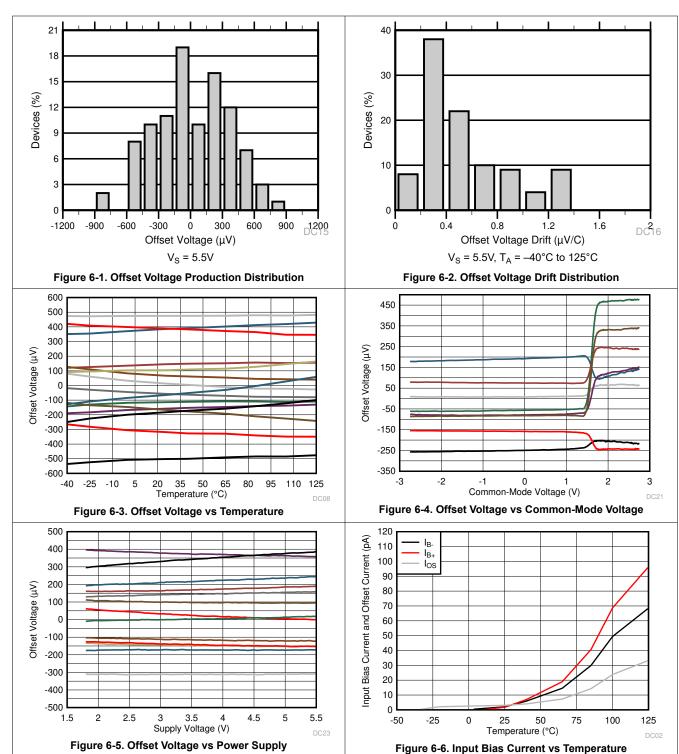
(2) Specified by design and characterization; not production tested.

(3) Disable time (t_{OFF}) and enable time (t_{ON}) are defined as the time interval between the 50% point of the signal applied to the SHDN pin and the point at which the output voltage reaches the 10% (disable) or 90% (enable) level.

(4) Full shutdown refers to the dual TLV9052S having both channels 1 and 2 disabled (SHDN1 = SHDN2 = V–) and the quad TLV9054S having all channels 1 to 4 disabled (SHDN12 = SHDN34 = V–). For partial shutdown, only one SHDN pin is exercised; in this mode, the internal biasing circuitry remains operational and the enable time is shorter.



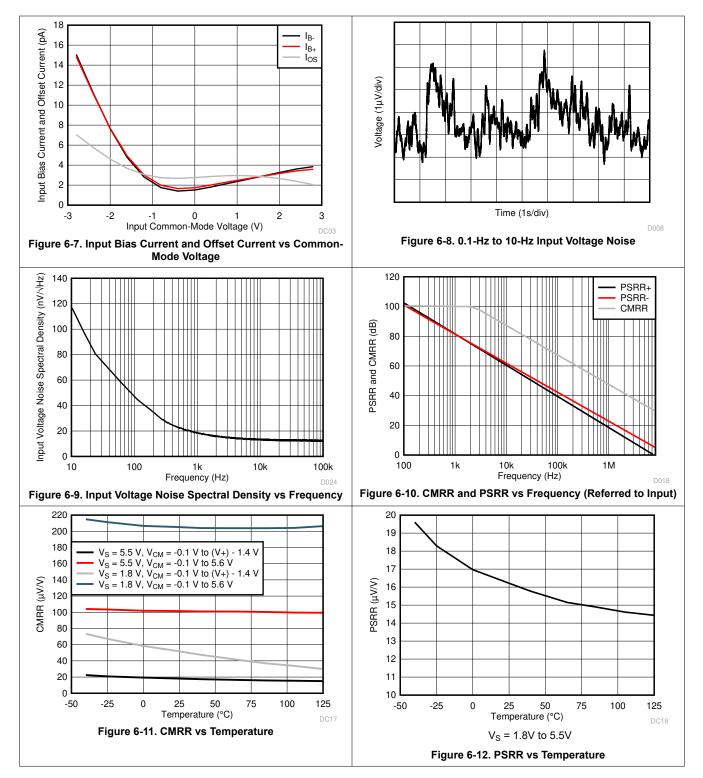
6.8 Typical Characteristics



at T_A = 25°C, V_S = 5.5V, R_L = 10k Ω connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted)

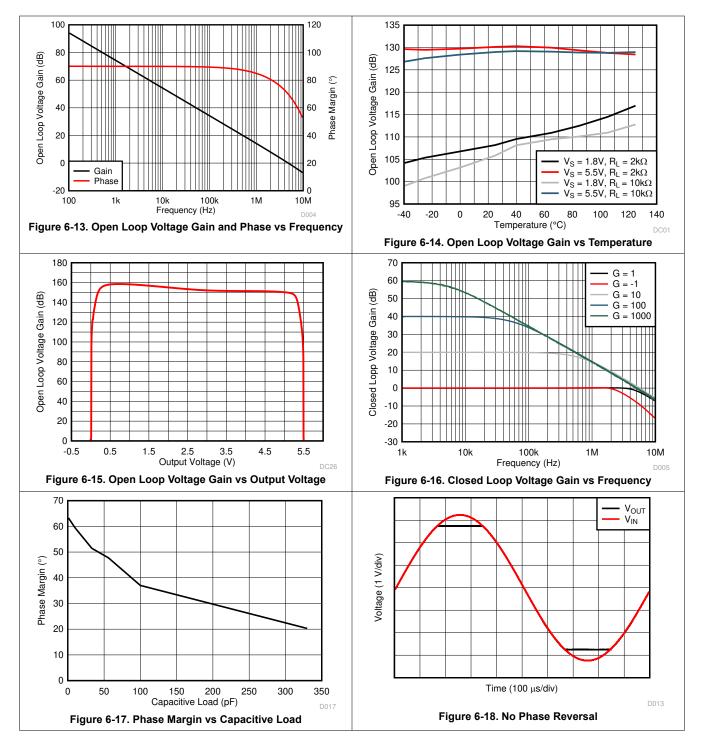


at $T_A = 25^{\circ}$ C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)



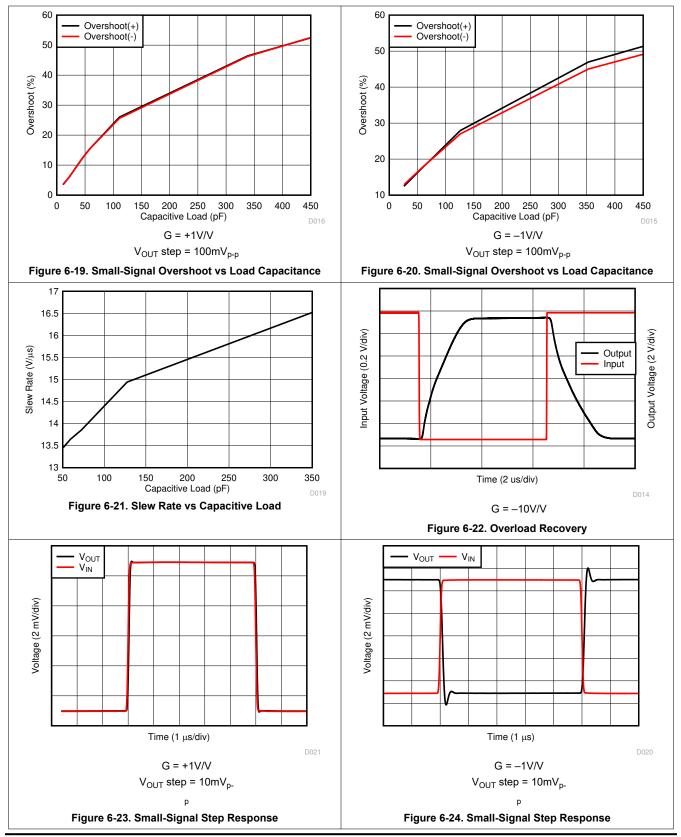


at $T_A = 25^{\circ}$ C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)





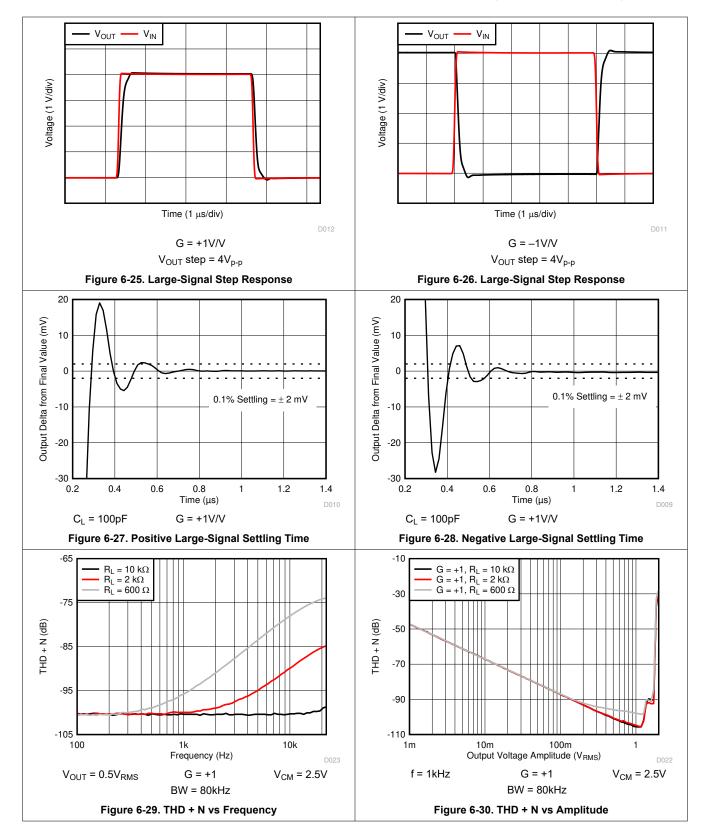
at $T_A = 25^{\circ}C$, $V_S = 5.5V$, $R_L = 10k\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)



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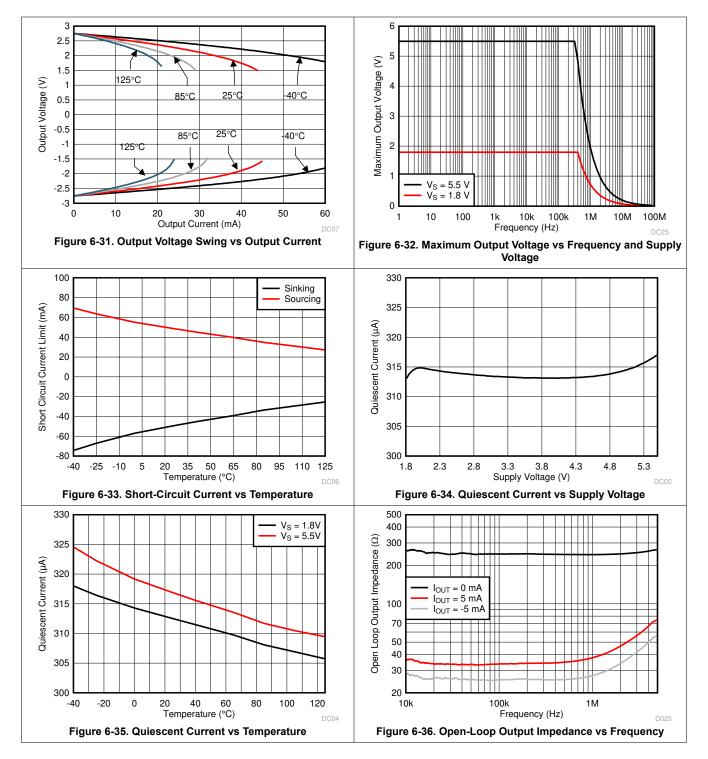
at $T_A = 25^{\circ}$ C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)



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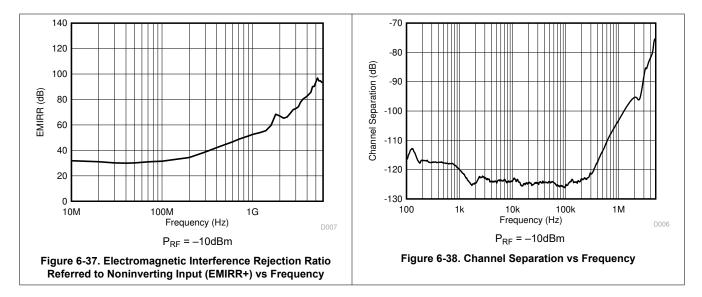


at $T_A = 25^{\circ}$ C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)





at $T_A = 25^{\circ}$ C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_S$ / 2, and $V_{OUT} = V_S$ / 2 (unless otherwise noted)



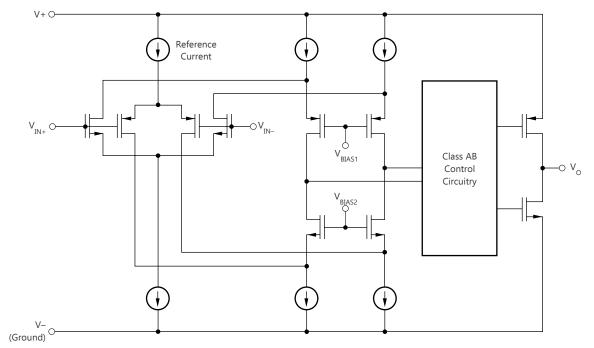


7 Detailed Description

7.1 Overview

The TLV905x devices are a 5MHz family of low-power, rail-to-rail input and output op amps. These devices operate from 1.8V to 5.5V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The input common-mode voltage range includes both rails and allows the TLV905x family to be used in virtually any single-supply application. The unique combination of a high slew rate and low quiescent current makes this family a potential choice for battery-powered motor-drive applications. Rail-to-rail input and output swing significantly increase dynamic range, especially in low-supply applications.

7.2 Functional Block Diagram





7.3 Feature Description

7.3.1 Operating Voltage

The TLV905x family of op amps is specified for operation from 1.8V to 6.0V. In addition, many specifications apply from -40° C to 125°C. Parameters that vary significantly with operating voltages or temperature are illustrated in the Section 6.8.

7.3.2 Rail-to-Rail Input

The input common-mode voltage range of the TLV905x family extends 100mV beyond the supply rails for the full supply voltage range of 1.8V to 6.0V. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the Section 7.2. The N-channel pair is active for input voltages close to the positive rail, typically (V+) - 1.4V to 200mV above the positive supply, whereas the P-channel pair is active for inputs from 200mV below the negative supply to approximately (V+) - 1.4V. There is a small transition region, typically (V+) - 1.2V to (V+) - 1V, in which both pairs are on. This 200-mV transition region can vary up to 200mV with process variation. Thus, the transition region (with both stages on) can range from (V+) - 1.4V to (V+) - 1.2V on the low end, and up to (V+) - 1V to (V+) - 0.8V on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD can degrade compared to device operation outside this region.

7.3.3 Rail-to-Rail Output

Designed as low-power, low-voltage operational amplifiers, the TLV905x family delivers a robust output drive capability. A class AB output stage with common-source transistors achieves full rail-to-rail output swing capability. For resistive loads of $10k\Omega$, the output swings to within 16mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

7.3.4 EMI Rejection

The TLV905x uses integrated electromagnetic interference (EMI) filtering to reduce the effects of EMI from sources such as wireless communications and densely-populated boards with a mix of analog signal chain and digital components. EMI immunity can be improved with circuit design techniques; the TLV905x benefits from these design improvements. Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10MHz to 6GHz. Figure 7-1 shows the results of this testing on the TLV905x. Table 7-1 shows the EMIRR IN+ values for the TLV905x at particular frequencies commonly encountered in real-world applications. The *EMI Rejection Ratio of Operational Amplifiers* application report contains detailed information on the topic of EMIRR performance as it relates to op amps and is available for download from www.ti.com.

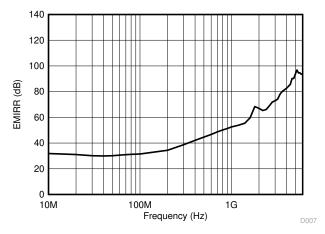


Figure 7-1. EMIRR Testing



FREQUENCY	APPLICATION OR ALLOCATION	EMIRR IN+
400MHz	Mobile radio, mobile satellite, space operation, weather, radar, ultra-high frequency (UHF) applications	41.8dB
900MHz	Global system for mobile communications (GSM) applications, radio communication, navigation, GPS (to 1.6GHz), GSM, aeronautical mobile, UHF applications	53.1dB
1.8GHz	GSM applications, mobile personal communications, broadband, satellite, L-band (1GHz to 2GHz)	71.8dB
2.4GHz	802.11b, 802.11g, 802.11n, Bluetooth [®] , mobile personal communications, industrial, scientific and medical (ISM) radio band, amateur radio and satellite, S-band (2GHz to 4GHz)	70.0dB
3.6GHz	Radiolocation, aero communication and navigation, satellite, mobile, S-band	81.2dB
5GHz	802.11a, 802.11n, aero communication and navigation, mobile communication, space and satellite operation, C-band (4GHz to 8GHz)	92.5dB

7.3.5 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the rated operating voltage, because of the high input voltage or high gain. After the device enters the saturation region, the output devices require time to return to the linear operating state. After the output devices return to their linear operating state, the device begins to slew at the specified slew rate. Therefore, the propagation delay (in case of an overload condition) is the sum of the overload recovery time and the slew time. The overload recovery time for the TLV905x family is approximately 300 ns.

7.3.6 Packages With an Exposed Thermal Pad

The TLV905x family is available in packages such as the WSON-8 (DSG) and WQFN-16 (RTE) which feature an exposed thermal pad. Inside the package, the die is attached to this thermal pad using an electrically conductive compound. For this reason, when using a package with an exposed thermal pad, the thermal pad must either be connected to V– or left floating. Attaching the thermal pad to a potential other then V– is not allowed, and the performance of the device is not verified when doing so.

7.3.7 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but can involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

Having a good understanding of this basic ESD circuitry and its relevance to an electrical overstress event is helpful. Figure 7-2 shows the ESD circuits contained in the TLV905x devices. The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power supply lines, where they meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

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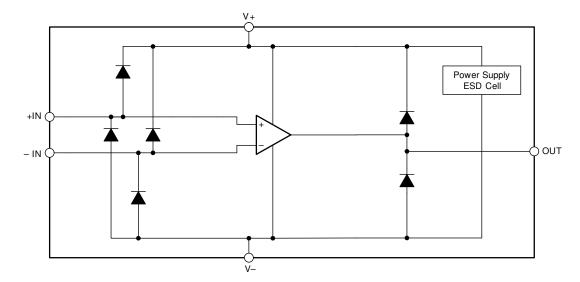


Figure 7-2. Equivalent Internal ESD Circuitry

7.3.8 Input Protection

The TLV905x family incorporates internal ESD protection circuits on all pins. For input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10mA, as shown in the *Section 6.1*. Figure 7-3 shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

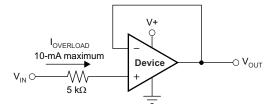


Figure 7-3. Input Current Protection

7.3.9 Shutdown Function

The TLV905xS devices feature \overline{SHDN} pins that disable the op amp, placing the device into a low-power standby mode. In this mode, the op amp consumes 1µA of maximum quiescent current, referred to as I_{QSD}. The \overline{SHDN} pins are active low, meaning that shutdown mode is enabled when the input to the \overline{SHDN} pin is a valid logic low.

The SHDN pins are referenced to the negative supply voltage of the op amp. The threshold of the shutdown feature lies around 800mV (typical) and does not change with respect to the supply voltage. Hysteresis has been included in the switching threshold for smooth switching characteristics. For shutdown behavior, the SHDN pins should be driven with valid logic signals. A valid logic low is defined as a voltage between V- and V- + 0.4V. A valid logic high is defined as a voltage between V- + 1.2V and V+. The shutdown pin circuitry includes a pull-up resistor, which will inherently pull the voltage of the pin to the positive supply rail if not driven. Thus, to enable the amplifier, the SHDN pins must either be left floating or driven to a valid logic high. To disable the amplifier, the SHDN pins must be driven to a valid logic low .While TI highly recommends that the shutdown pin be connected to a valid high or a low voltage or driven, TI has included a pull-up resistor connected to VCC. The maximum voltage allowed at the SHDN pins is (V+) + 0.5V. Exceeding this voltage level will damage the device.

The SHDN pins are high-impedance CMOS inputs. Dual op amp versions are independently controlled and quad op amp versions are controlled in pairs with logic inputs. For battery-operated applications, this feature

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may be used to greatly reduce the average current and extend battery life. The enable time is 35 μ s for full shutdown of all channels; disable time is 6 μ s. When disabled, the output assumes a high-impedance state. This architecture allows the TLV905xS to be operated as a gated amplifier (or to have the device output multiplexed onto a common analog output bus). Shutdown time (t_{OFF}) depends on loading conditions and increases as load resistance increases. For shutdown (disable) within a specific shutdown time, the specified 10k Ω load to midsupply (V_S / 2) is required. If using the TLV905xS without a load, the resulting turnoff time is significantly increased.

7.4 Device Functional Modes

The TLV905x family is operational when the power-supply voltage is between 1.8V (±0.9V) and 6.0V (±3.0V).

The TLV905xS devices feature a shutdown mode and are shutdown when a valid logic low is applied to the shutdown pin.



8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TLV905x family features 5MHz bandwidth and very high slew rate of 15V/µs with only 330µA of supply current per channel, providing excellent AC performance at very low-power consumption. DC applications are well served with a very low input noise voltage of $15nV/\sqrt{Hz}$ at 10kHz, low input bias current, and a typical input offset voltage of 0.33mV.

8.2 Typical Low-Side Current Sense Application

Figure 8-1 shows the TLV905x configured in a low-side current sensing application.

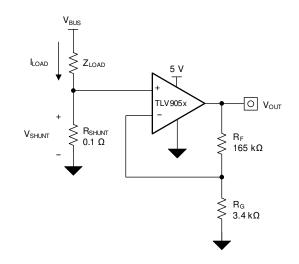


Figure 8-1. TLV905x in a Low-Side, Current-Sensing Application

8.2.1 Design Requirements

The design requirements for this design are:

- Load current: 0A to 1A
- Output voltage: 4.95V
- Maximum shunt voltage: 100mV



(1)

8.2.2 Detailed Design Procedure

The transfer function of the circuit in Figure 8-1 is given in Equation 1.

The load current (I_{LOAD}) produces a voltage drop across the shunt resistor (R_{SHUNT}). The load current is set from 0A to 1A. To keep the shunt voltage below 100mV at maximum load current, the largest shunt resistor is defined using Equation 2.

$$R_{SHUNT} = \frac{V_{SHUNT} MAX}{I_{LOAD} MAX} = \frac{100 \, mV}{1 \, A} = 100 \, m\Omega \tag{2}$$

Using Equation 2, R_{SHUNT} equals 100 m Ω . The voltage drop produced by I_{LOAD} and R_{SHUNT} is amplified by the TLV905x device to produce an output voltage of approximately 0V to 4.95V. Equation 3 calculates the gain required for the TLV905x device to produce the required output voltage.

$$Gain = \frac{(V_{OUT_MAX} - V_{OUT_{MIN}})}{(V_{IN_MAX} - V_{IN_MIN})}$$
(3)

Using Equation 3, the required gain equals 49.5V/V, which is set with the R_F and R_G resistors. Equation 4 sizes the R_F and R_G , resistors to set the gain of the TLV905x device to 49.5V/V.

$$Gain = 1 + \frac{(R_F)}{(R_G)} \tag{4}$$

Selecting R_F to equal 165k Ω and R_G to equal 3.4k Ω provides a combination that equals approximately 49.5V/V. Figure 8-2 shows the measured transfer function of the circuit shown in Figure 8-1.

8.2.3 Application Curve

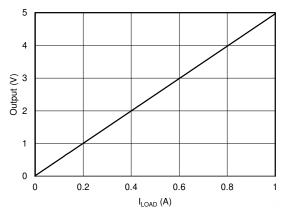


Figure 8-2. Low-Side, Current-Sense Transfer Function



8.3 Power Supply Recommendations

The TLV905x family is specified for operation from 1.8V to 6.0V (\pm 0.9V to \pm 3.0V); many specifications apply from -40°C to 125°C. The *Section 6.8* section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

CAUTION

Supply voltages larger than 7V can permanently damage the device; see the Section 6.1 table.

Place 0.1µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more-detailed information on bypass capacitor placement, see the *Section 8.4.2* section.

8.4 Layout

8.4.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and of the op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Take care to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see *Circuit Board Layout Techniques*.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As illustrated in Figure 8-4, keeping R_F and R_G close to the inverting input minimizes parasitic capacitance on the inverting input.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts resulting from moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.



8.4.2 Layout Example

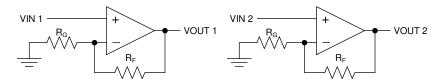
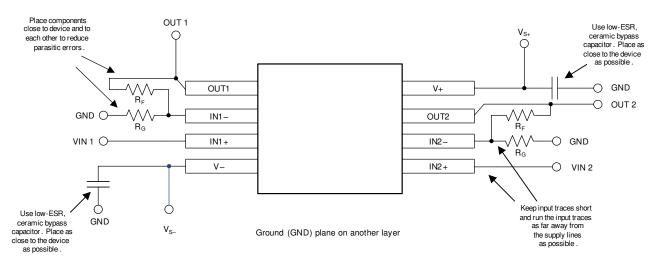
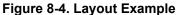


Figure 8-3. Schematic Representation for Figure 8-4







9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, TLVx313 Low-Power, Rail-to-Rail In/Out, 500-µV Typical Offset, 1MHz Operational Amplifier for Cost-Sensitive Systems
- Texas Instruments, TLVx314 3MHz, Low-Power, Internal EMI Filter, RRIO, Operational Amplifier
- Texas Instruments, EMI Rejection Ratio of Operational Amplifiers
- Texas Instruments, QFN/SON PCB Attachment
- Texas Instruments, Quad Flatpack No-Lead Logic Packages
- Texas Instruments, Circuit Board Layout Techniques
- Texas Instruments, Single-Ended Input to Differential Output Conversion Circuit Reference Design

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision I (November 2022) to Revision J (February 2024)	Page
•	Changed pins 3 and 4 the TLV9051S DBV pin diagram	3
•	Added shutdown section into the Electrical Characteristics table	11



С	hanges from Revision H (October 2019) to Revision I (November 2022)	Page
•	Increased maximum supply voltage in Absolute Maximum Ratings from 6 \	/ to 7 V
•	Added maximum limits for input bias current and input offset current	

С	hanges from Revision G (September 2019) to Revision H (October 2019)	Page
•	Added new human-body model and charged-device model ratings for TLV9051 X2SON package to the	ESD
	Ratings	9
•	Added Packages With an Exposed Thermal Pad section to Feature Description section	

CI	hanges from Revision F (June 2019) to Revision G (September 2019)	Page
•	Deleted preview tags for all TLV9051 packages	1
•	Deleted preview tags for the TLV9052 SOT-23, 8) - DDF package	1
•	Added link to Shutdown Function section in all of the SHDN pin function rows	3
•	Added EMI Rejection section to Feature Description section	21
•	Added clarification to the Shutdown Function section	23

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the mostcurrent data available for the designated devices. This data is subject to change without notice and without revision of this document. For browser-based versions of this data sheet, see the left-hand navigation pane.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV9051IDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	T51D	Samples
TLV9051IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	T51	Samples
TLV9051IDPWR	ACTIVE	X2SON	DPW	5	3000	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	FH	Samples
TLV9051SIDBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	T51S	Samples
TLV9052IDDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T052	Samples
TLV9052IDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU SN NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1PWX	Samples
TLV9052IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL9052	Samples
TLV9052IDSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	9052	Samples
TLV9052IPWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL9052	Samples
TLV9052SIDGSR	ACTIVE	VSSOP	DGS	10	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	T052	Samples
TLV9052SIRUGR	ACTIVE	X2QFN	RUG	10	3000	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	FPF	Samples
TLV9054IDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV9054D	Samples
TLV9054IPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU SN	Level-2-260C-1 YEAR	-40 to 125	(T9054PW, TLV9054)	Samples
TLV9054IRTER	ACTIVE	WQFN	RTE	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T54RT	Samples
TLV9054IRUCR	ACTIVE	QFN	RUC	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1FF	Samples
TLV9054SIRTER	ACTIVE	WQFN	RTE	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T9054S	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. **PREVIEW:** Device has been announced but is not in production. Samples may or may not be available. **OBSOLETE:** TI has discontinued the production of the device.



PACKAGE OPTION ADDENDUM

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLV9051, TLV9052 :

• Automotive : TLV9051-Q1, TLV9052-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV9051IDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV9051IDCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
TLV9051IDPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q2
TLV9051SIDBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV9052IDDFR	SOT-23- THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV9052IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV9052IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV9052IDSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV9052IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLV9052SIDGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV9052SIRUGR	X2QFN	RUG	10	3000	178.0	8.4	1.75	2.25	0.56	4.0	8.0	Q1
TLV9054IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLV9054IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLV9054IRTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV9054IRUCR	QFN	RUC	14	3000	180.0	9.5	2.16	2.16	0.5	4.0	8.0	Q2



15-Oct-2024

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	· · /	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV9054SIRTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2



PACKAGE MATERIALS INFORMATION

15-Oct-2024



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV9051IDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV9051IDCKR	SC70	DCK	5	3000	210.0	185.0	35.0
TLV9051IDPWR	X2SON	DPW	5	3000	205.0	200.0	33.0
TLV9051SIDBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
TLV9052IDDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
TLV9052IDGKR	VSSOP	DGK	8	2500	356.0	356.0	35.0
TLV9052IDR	SOIC	D	8	2500	356.0	356.0	35.0
TLV9052IDSGR	WSON	DSG	8	3000	210.0	185.0	35.0
TLV9052IPWR	TSSOP	PW	8	2000	356.0	356.0	35.0
TLV9052SIDGSR	VSSOP	DGS	10	2500	366.0	364.0	50.0
TLV9052SIRUGR	X2QFN	RUG	10	3000	205.0	200.0	33.0
TLV9054IDR	SOIC	D	14	2500	356.0	356.0	35.0
TLV9054IPWR	TSSOP	PW	14	2000	353.0	353.0	32.0
TLV9054IRTER	WQFN	RTE	16	3000	367.0	367.0	35.0
TLV9054IRUCR	QFN	RUC	14	3000	205.0	200.0	30.0
TLV9054SIRTER	WQFN	RTE	16	3000	367.0	367.0	35.0

D0014A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



D0014A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0014A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DGS0010A



PACKAGE OUTLINE

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187, variation BA.



DGS0010A

EXAMPLE BOARD LAYOUT

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DGS0010A

EXAMPLE STENCIL DESIGN

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

GENERIC PACKAGE VIEW

X2SON - 0.4 mm max height PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



4211218-3/D

DPW0005A



PACKAGE OUTLINE

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.



DPW0005A

EXAMPLE BOARD LAYOUT

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).



DPW0005A

EXAMPLE STENCIL DESIGN

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



DDF0008A



PACKAGE OUTLINE

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.



DDF0008A

EXAMPLE BOARD LAYOUT

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



4. Publication IPC-7351 may have alternate designs.

5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DDF0008A

EXAMPLE STENCIL DESIGN

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



^{6.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



^{7.} Board assembly site may have different recommendations for stencil design.

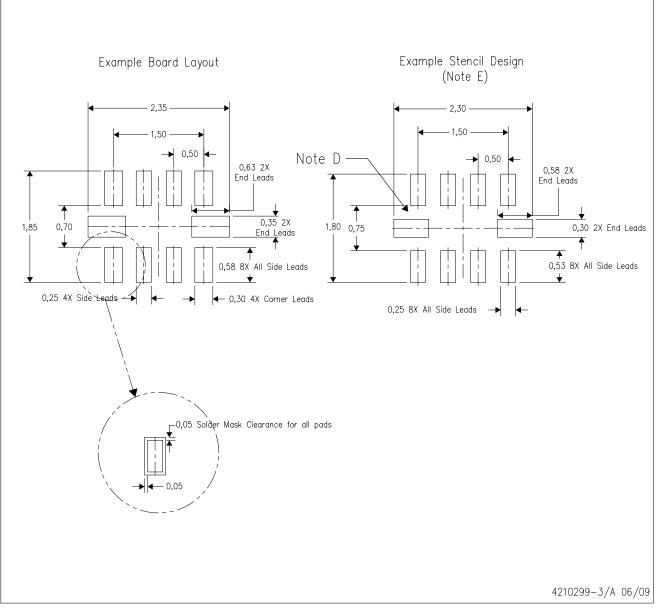
MECHANICAL DATA



B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No-Lead) package configuration.
D. This package complies to JEDEC MO-288 variation X2EFD.



RUG (R-PQFP-N10)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
- E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DCK0005A



PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



DCK0005A

EXAMPLE BOARD LAYOUT

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

Publication IPC-7351 may have alternate designs.
 Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DCK0005A

EXAMPLE STENCIL DESIGN

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

10. Board assembly site may have different recommendations for stencil design.



DBV0006A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- 5. Refernce JEDEC MO-178.



DBV0006A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBV0006A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DSG 8

2 x 2, 0.5 mm pitch

GENERIC PACKAGE VIEW

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





DSG0008A



PACKAGE OUTLINE

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.

3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



DSG0008A

EXAMPLE BOARD LAYOUT

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

 This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

 Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



DSG0008A

EXAMPLE STENCIL DESIGN

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



PW0014A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



PW0014A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PW0014A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



PW0008A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



PW0008A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PW0008A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

RUC 14

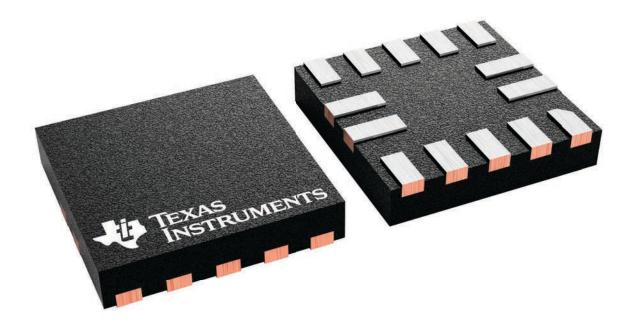
2 x 2, 0.4 mm pitch

GENERIC PACKAGE VIEW

X2QFN - 0.4 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



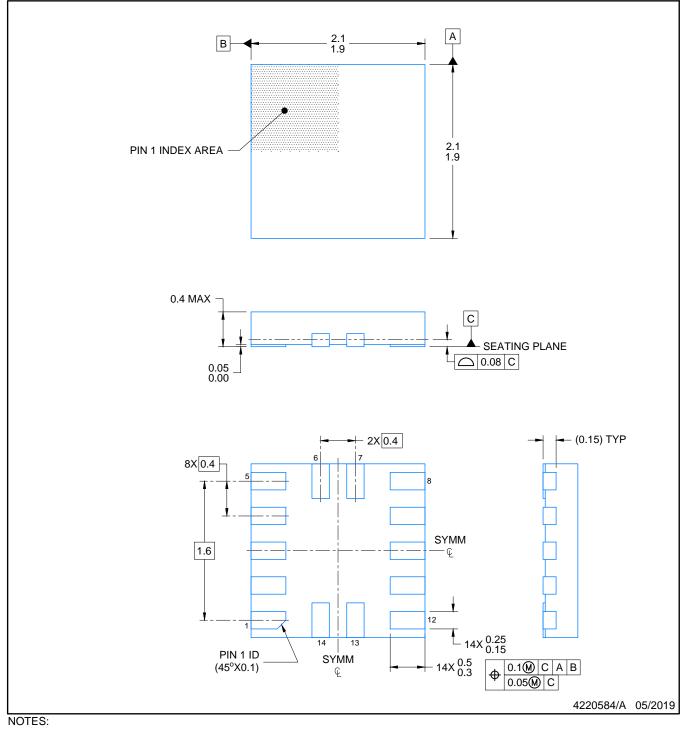


RUC0014A

PACKAGE OUTLINE

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.

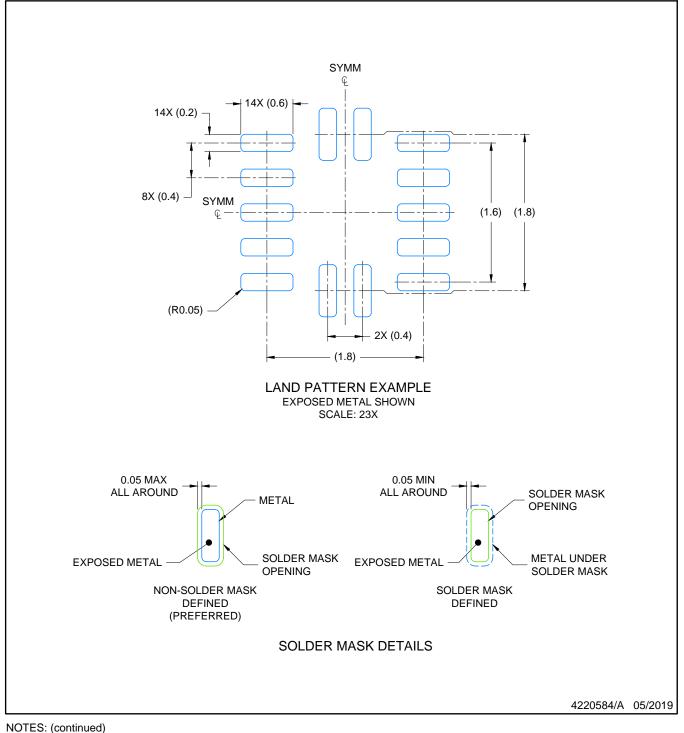


RUC0014A

EXAMPLE BOARD LAYOUT

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

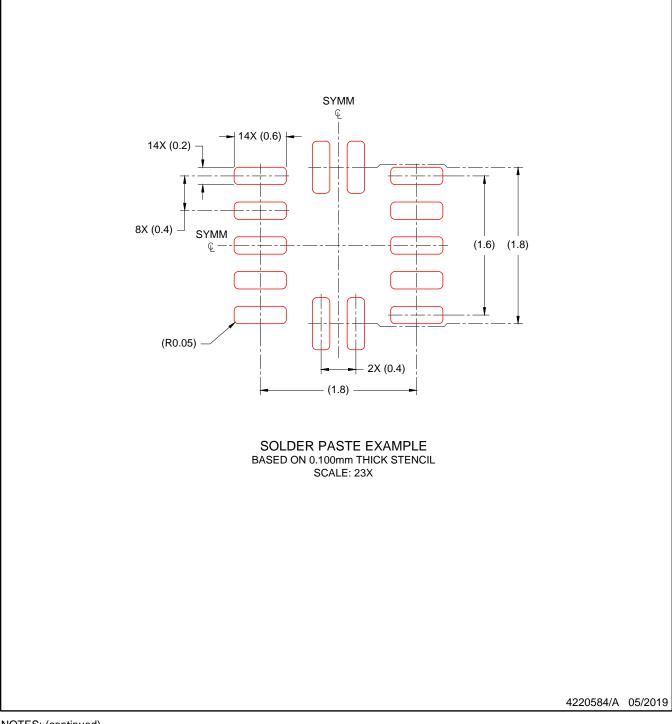


RUC0014A

EXAMPLE STENCIL DESIGN

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



DBV0005A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



DBV0005A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBV0005A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DGK0008A



PACKAGE OUTLINE

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.



DGK0008A

EXAMPLE BOARD LAYOUT

[™] VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown
- on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.



DGK0008A

EXAMPLE STENCIL DESIGN

[™] VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

12. Board assembly site may have different recommendations for stencil design.



RTE 16

3 x 3, 0.5 mm pitch

GENERIC PACKAGE VIEW

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





RTE0016C



PACKAGE OUTLINE

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



RTE0016C

EXAMPLE BOARD LAYOUT

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



 This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



RTE0016C

EXAMPLE STENCIL DESIGN

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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